

Glass Passivated Standard Recovery Diodes (Stud Version), 16A

FEATURES

- Glass passivated chips
- High surge current capability
- Stud cathode and stud anode version
- Wide current range
- Voltage up to 1600V V_{RRM}
- RoHS compliant

TYPICAL APPLICATIONS

- Battery charges
- Converters
- Power supplies
- Machine tool controls



DO-203AA(DO-4)

PRODUCT SUMMARY

$I_{F(AV)}$	16A
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MAJOR RATINGS AND CHARACTERISTICS

PARAMETER	TEST CONDITIONS	VALUES	UNIT
$I_{F(AV)}$	T_C	16	A
		140	$^{\circ}\text{C}$
$I_{F(RMS)}$		25	A
I_{FSM}	50 HZ	350	A
	60 HZ	370	
I^2t	50 HZ	612	A^2s
	60 HZ	558	
V_{RRM}	Range	200 to 1600	V
T_J		-65 to 175	$^{\circ}\text{C}$

ELECTRICAL SPECIFICATIONS

VOLTAGE RATINGS

TYPE NUMBER	VOLTAGE CODE	V_{RRM} , MAXIMUM REPETITIVE PEAK REVERSE VOLTAGE V	V_{RSM} , MAXIMUM NON-REPETITIVE PEAK VOLTAGE V	$V_{R(BR)}$, MINIMUM AVALANCHE VOLTAGE $V^{(1)}$	V_{RRM} , MAXIMUM AT $T_J=175^{\circ}\text{C}$ mA
16D(R)	02	200	275	-	12
	04	400	500	500	
	06	600	725	750	
	08	800	950	950	
	10	1000	1200	1150	
	12	1200	1400	1350	
	16	1600	1800	1750	

Note

(1) Avalanche version only available from V_{RRM} 400V to 1600V

FORWARD CONDUCTION							
PARAMETER	SYMBOL	TEST CONDITIONS			VALUES	UNIT	
Maximum average forward current at case temperature	I _{F(AV)}	180° conduction, half sine wave			16	A	
					140	°C	
Maximum RMS forward current	I _{F(RMS)}				25	A	
Maximum on-repetitive peak reverse power	P _R ⁽¹⁾	10μs square pulse, T _J = T _J maximum			15	K/W	
Maximum peak, one-cycle forward, non-reptitive surge current	I _{FSM}	t = 10ms	No voltage reapplied	Sinusoidal half wave, initial T _J = T _J maximum	350	A	
		t = 8.3ms			370		
		t = 10ms	100% V _{RRM} reapplied		295		A ² s
		t = 8.3ms			310		
Maximum I ² t for fusing	I ² t	t = 10ms	No voltage reapplied		612		
		t = 8.3ms			558		
		t = 10ms	100% V _{RRM} reapplied		435		
		t = 8.3ms			395		
Maximum I ² /t for fusing	I ² √t	t = 0.1 to 10 ms, no voltage reapplied			6125	A ² √s	
Maximum forward voltage drop	V _{FM}	I _{pk} = 50 A, T _J = 25 °C, t _p = 400μs rectangular wave			1.25	V	

Note

(1) Avalanche only for avalanche version, all other parameters the same as 16D

THERMAL AND MECHANICAL SPECIFICATIONS				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum junction operating temperature range	T_J		- 65 to 175	°C
Maximum storage temperature range	T_{stg}		- 65 to 200	
Maximum thermal resistance, junction to case	R_{thJC}	DC operation	1.6	K/W
Maximum thermal resistance case to heatsink	R_{thCS}	Mounting surface, smooth, flat and greased	0.5	
Allowable mounting torque		Not lubricated threads	1.5 ⁺⁰ _{-10%} (13)	N · m (lbf · in)
		Lubricated threads	1.2 ⁺⁰ _{-10%} (10)	N · m (lbf · in)
Approximate weight			6	g
			0.21	oz.
Case style		See dimensions - link at the end of datasheet	DO-203AA (DO-4)	

ΔR_{thJC} CONDUCTION				
CONDUCTION ANGEL	SINUSOIDAL CONDUCTION	RECTANGULAR CONDUCTION	TEST CONDUCTIONS	UNITS
180°	0.31	0.23	$T_J = T_J$ maximum	K/W
120°	0.38	0.40		
90°	0.49	0.54		
60°	0.72	0.75		
30°	1.20	1.21		

Note

• The table above shows the increment of thermal resistance R_{thJC} when devices operate at different conduction angles than DC

Nell High Power Products

Fig.1 Current Ratings Characteristics

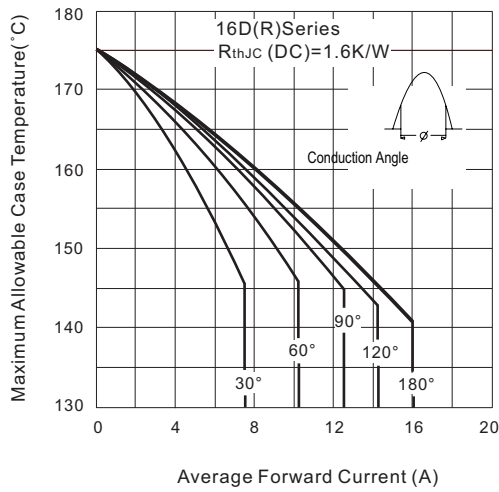


Fig.2 Current Ratings Characteristics

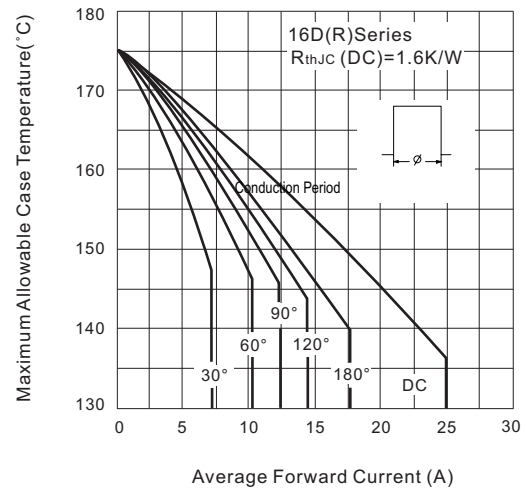


Fig. 3 Forward Power Loss Characteristics

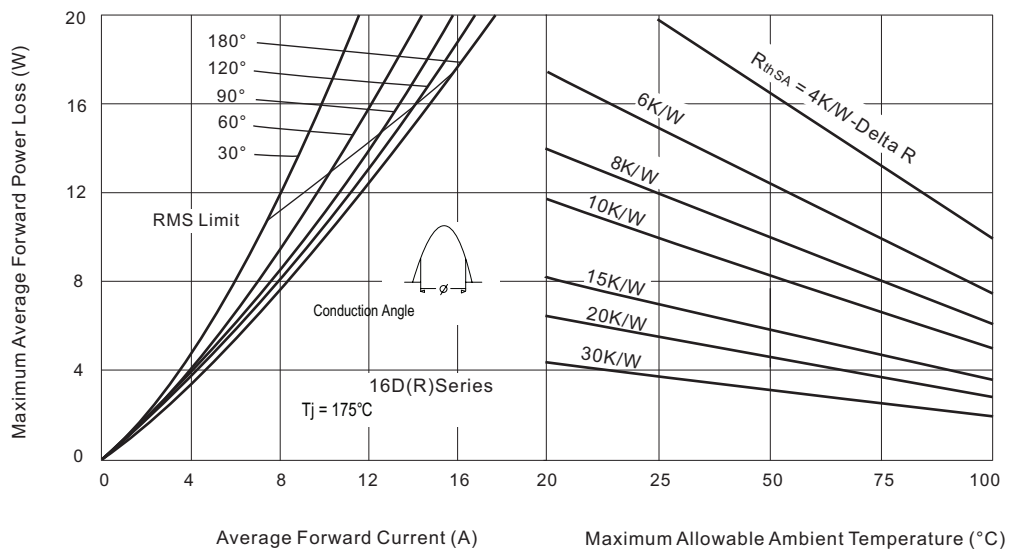


Fig. 4 Forward Power Loss Characteristics

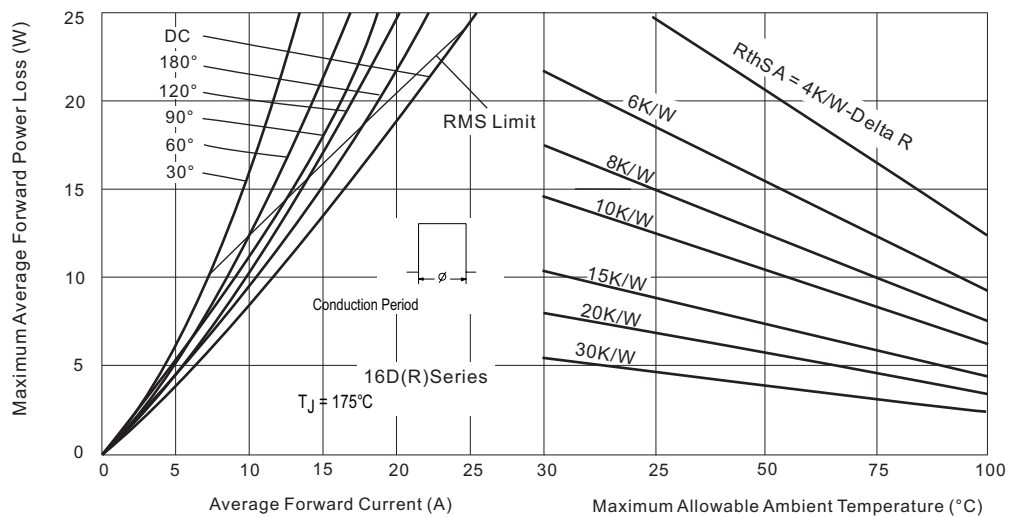


Fig. 5 Maximum Non-Repetitive Surge Current

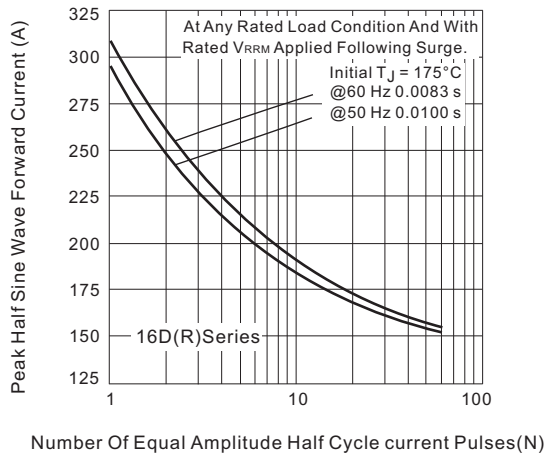


Fig. 6 Forward Voltage Drop Characteristics

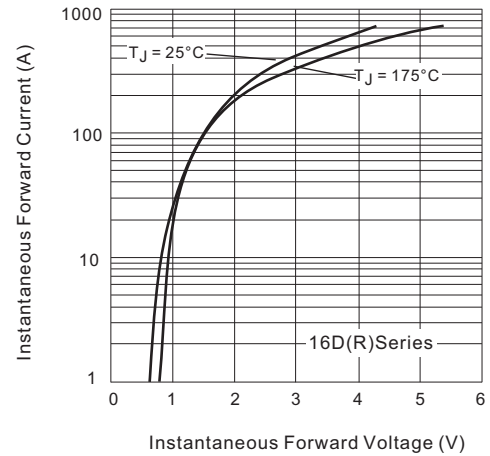


Fig.7 Maximum Non-Repetitive Surge Current

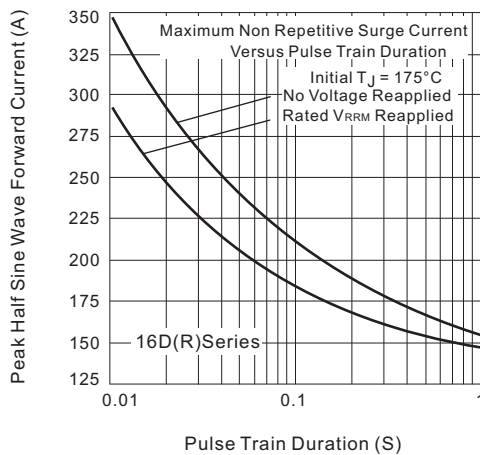
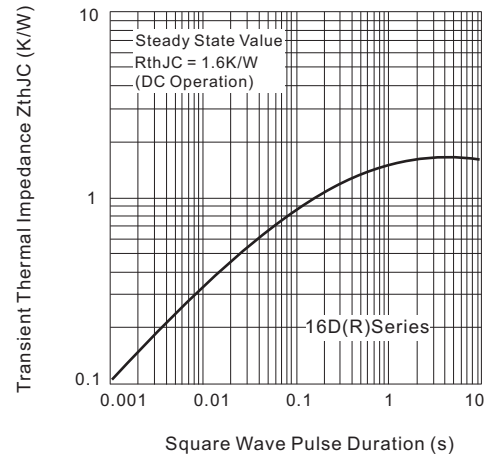


Fig.8 Thermal Impedance Z_{thJC} Characteristics



ORDERING INFORMATION TABLE

Device code	16	D	R	12	M
	①	②	③	④	⑤
①	-	Current rating: Code = $I_{F(AV)}$			
②	-	D = Standard recovery device			
③	-	None = Stud normal polarity (cathode to stud) R = Stud reverse polarity (anode to stud)			
④	-	Voltage code $\times 100 = V_{RRM}$ (see Voltage Ratings table)			
⑤	-	None = Stud base DO-203AA (DO-4) #10-32 UNF-2A M = Stud base DO-203AA (DO-4) M5 $\times$ 0.8 (not available for avalanche diodes)			

